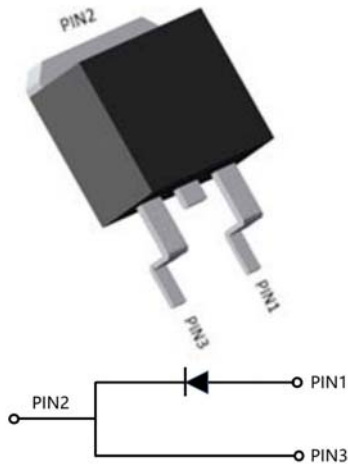


Silicon Carbide Schottky Diode

V_{RRM}	1200V
I_F (135°C)	14A
Q_C	53nC



Features

- Positive temperature coefficient
- Temperature-independent switching
- Maximum working temperature at 175 °C
- Unipolar devices and zero reverse recovery current
- Zero forward recovery current
- Essentially no switching losses
- Reduction of heat sink requirements
- High-frequency operation
- Reduction of EMI

Typical Applications

Typical applications are in power factor correction(PFC), solar inverter, uninterruptible power supply, motor drives, photovoltaic inverter, electric car and charger.

Mechanical Data

- **Package:** TO-263
- **Terminals:** Tin plated leads
- **Polarity:** As marked

■Maximum Ratings ($T_c=25^\circ\text{C}$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Device marking code			D112010BQG2
Reverse voltage (repetitive peak) @ $T_j=25^\circ\text{C}$	V_{RRM}	V	1200
Reverse voltage (Surge Peak) @ $T_j=25^\circ\text{C}$	V_{RSM}	V	1200
Reverse voltage (DC) @ $T_j=25^\circ\text{C}$	V_{DC}	V	1200
Continuous forward current @ $T_c=25^\circ\text{C}$	I_F	A	33
Continuous forward current @ $T_c=135^\circ\text{C}$			14
Continuous forward current @ $T_c=141^\circ\text{C}$			10
Non-repetitive peak forward surge current @ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$, Half Sine Wave	I_{FSM}	A	85
Power Dissipation@ $T_c=25^\circ\text{C}$	P_{TOT}	W	158
Power Dissipation@ $T_c=110^\circ\text{C}$			68
i^2t Value@ $T_c=25^\circ\text{C}$, $t_p=10\text{ms}$	$\int i^2 dt$	A^2S	36
Operating junction and Storage temperature range	T_j, T_{stg}	$^\circ\text{C}$	-55 to +175



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■Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Typ.	Max.
Forward voltage drop	V_F	V	$I_F=10A, T_j=25^{\circ}C$	1.42	1.54
			$I_F=10A, T_j=175^{\circ}C$	2.1	-
Reverse leakage current	I_R	μA	$V_R=1200V, T_j=25^{\circ}C$	1.3	13
			$V_R=1200V, T_j=175^{\circ}C$	6	-
Total capacitive charge	Q_C	nC	$V_R=800V, T_j=25^{\circ}C$, $Q_C=\int_0^{V_R} I_C(V)dV$	53	-
Total capacitance	C	pF	$V_R=0V, f=1MHZ$	700	-
			$V_R=400V, f=1MHZ$	49	-
			$V_R=800V, f=1MHZ$	39	-
Capacitance Stored Energy	E_C	μJ	$V_R=800V$	14	-

■Thermal Characteristics ($T_a=25^{\circ}C$ Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	VALUE
Thermal resistance	$R_{\theta J-C}$	$^{\circ}C/W$	0.95

■Typical Characteristics

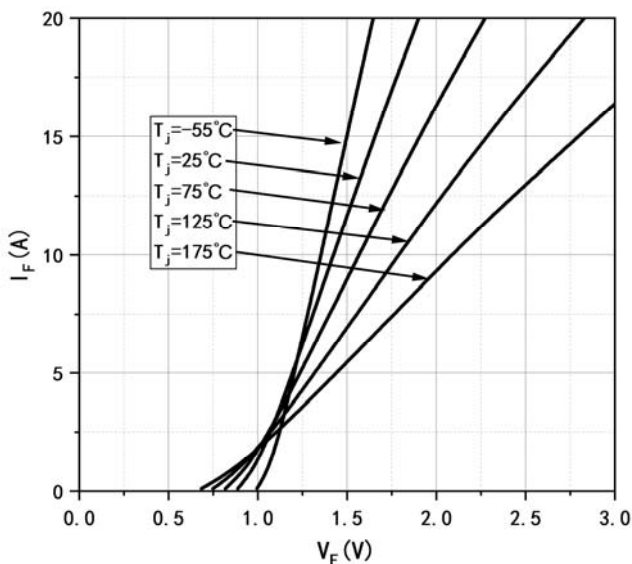


Figure 1. Forward Characteristics

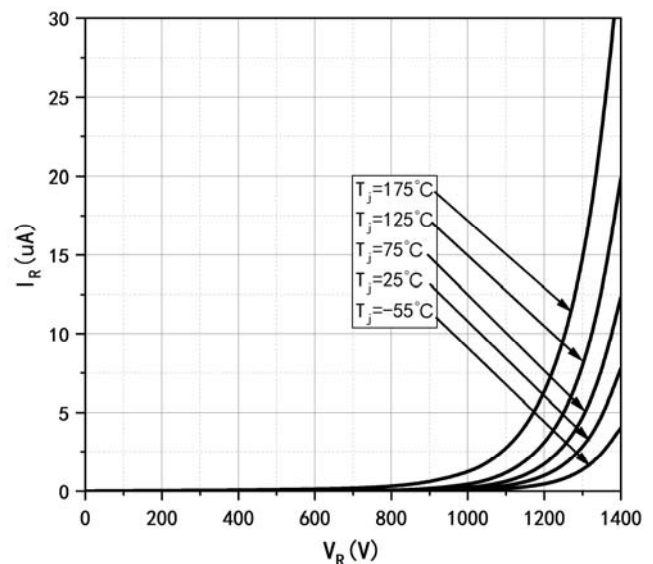


Figure 2. Reverse Characteristic



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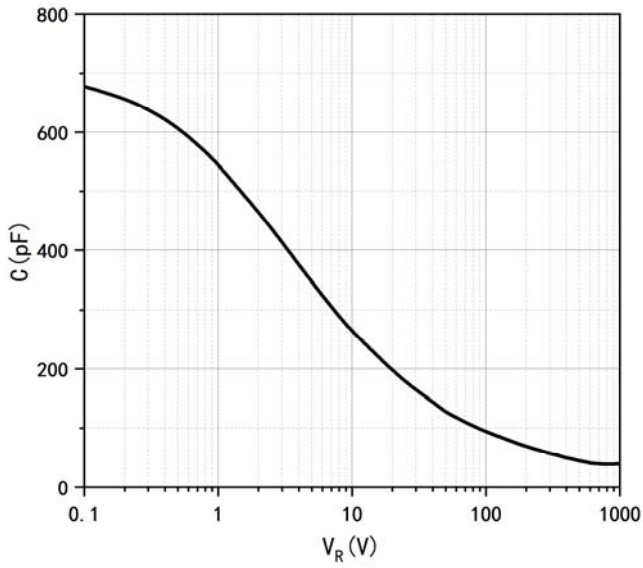


Figure 3. Capacitance vs. Reverse Voltage

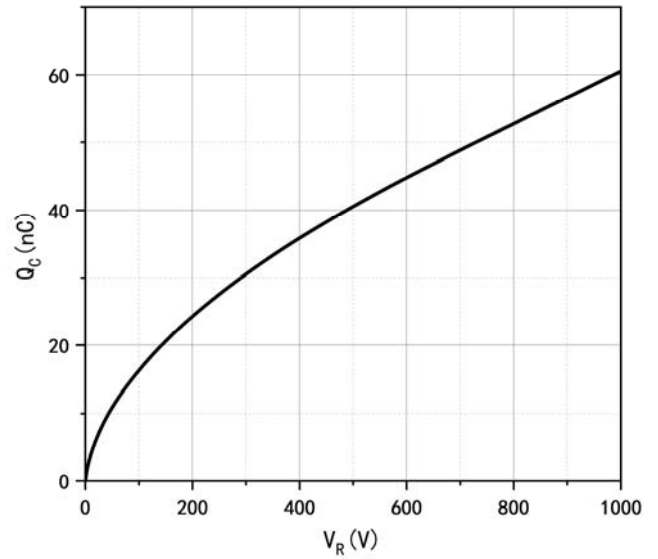


Figure 4. Total Capacitance Charge vs. Reverse Voltage

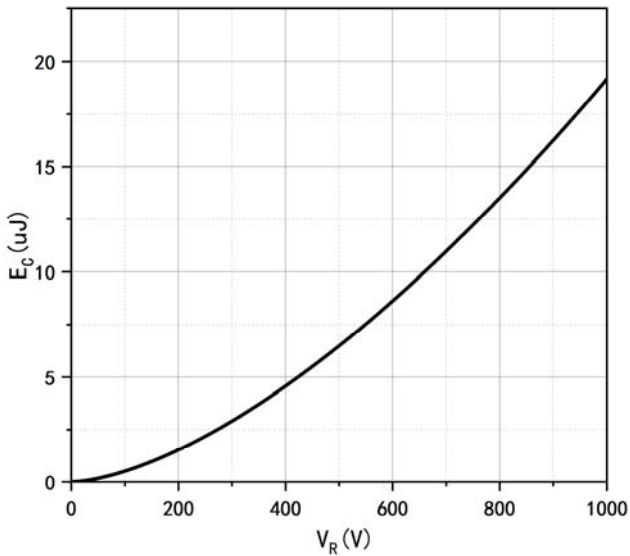


Figure 5. Capacitance Stored Energy

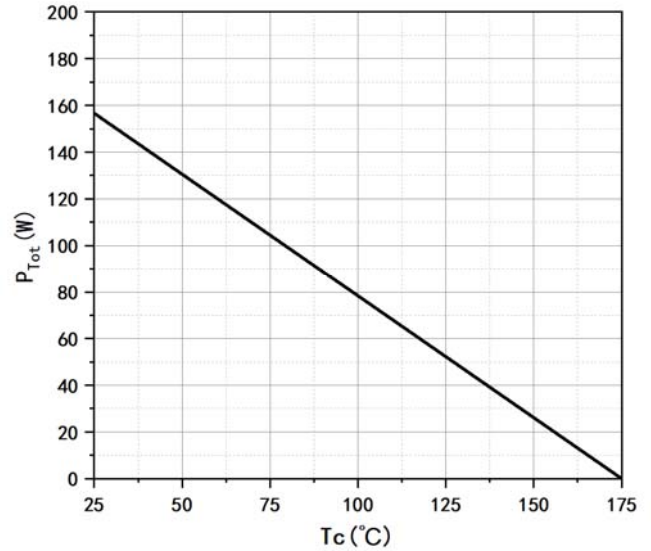


Figure 6. Power Derating

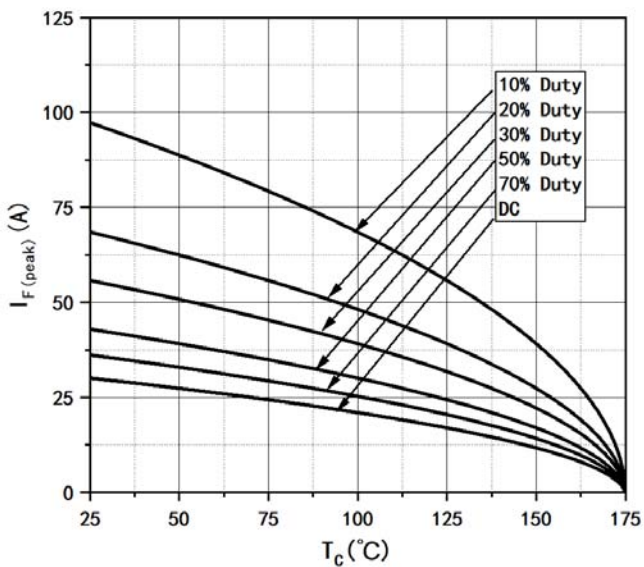


Figure 7. Current Derating

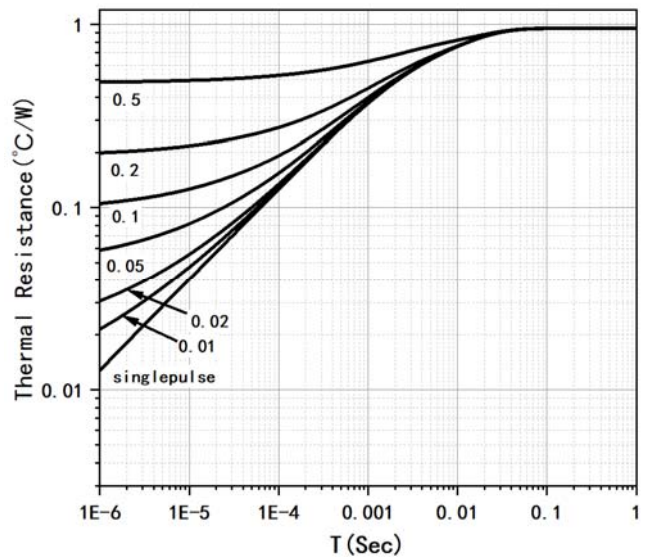
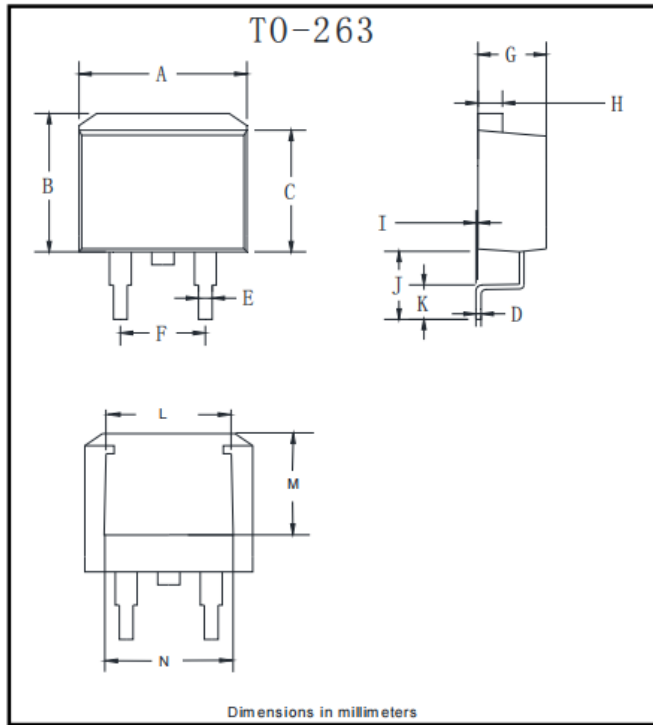


Figure 8. Transient Thermal Impedance



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■Outline Dimensions



TO-263		
Dim	Min	Max
A	9.5	11.5
B	9.7	10.5
C	8.4	9.0
D	0.28	0.64
E	0.68	0.94
F	4.55	5.6
G	4.04	5.10
H	1.14	1.4
I	0	0.2
J	4.9	6.05
K	1.79	2.79
L	7.3	7.9
M	6.2	6.8
N	7.6	8.2



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